# 4V Drive Pch MOS FET RSL020P03

#### Structure

Silicon P-channel MOS FET

#### Features

- 1) Low On-resistance.
- 2) High speed switching.

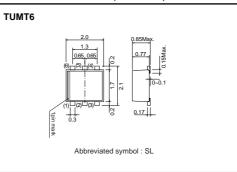
#### Applications

Switching

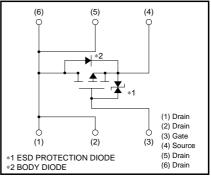
#### Packaging specifications

	Package	Taping	
Туре	Code	TR	
	Basic ordering unit (pieces)	3000	
RSL020P03	0		

#### •External dimensions (Unit : mm)



#### Inner circuit



#### ●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-30	V	
Gate-source voltage		Vgss	±20	V	
Duala aumont	Continuous	lo	±2	А	
Drain current	Pulsed	DP *1	±8	А	
Source current	Continuous	ls	-0.8	А	
(Body diode)	Pulsed	Isp *1	-8	А	
Total power dissipation		Pp *2	1	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board

#### \*2 Woullied on a cerainic boar

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W
* Mounted on a coromic board			

\* Mounted on a ceramic board

## Transistors

### •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	V(BR) DSS	-30	-	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	-1	μA	$V_{DS}$ = -30V, $V_{GS}$ =0V
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$
Static drain-source on-state resistance		-	80	120	mΩ	I <sub>D</sub> = -2A, V <sub>GS</sub> = -10V
	$R_{DS(on)^*}$	-	125	190	mΩ	I <sub>D</sub> =-1A, V <sub>GS</sub> = -4.5V
		-	140	210	mΩ	I <sub>D</sub> = -1A, V <sub>GS</sub> = -4.0V
Forward transfer admittance	Y <sub>fs</sub> *	1.4	-	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A
Input capacitance	Ciss	-	350	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	-	80	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	50	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	11	_	ns	V <sub>DD</sub> ≒ −15V
Rise time	tr *	-	11	_	ns	$I_{D} = -1A$
Turn-off delay time	t <sub>d (off)</sub> *	-	35	_	ns	VGs= –10V R∟=15Ω
Fall time	t <sub>f</sub> *	-	11	_	ns	$R_G = 10\Omega$
Total gate charge	Qg	-	3.9	-	nC	V <sub>DD</sub> ≒–15V V <sub>GS</sub> =–5V
Gate-source charge	Qgs	-	1.3	_	nC	ID=-2A
Gate-drain charge	Q <sub>gd</sub>	_	1.1	_	nC	R∟=7.5Ω R <sub>G</sub> =10Ω

### •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	Ι	-	-1.2	V	Is= -0.8A, V <sub>GS</sub> =0V

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